N-Channel 30-V (D-S) MOSFET

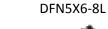
Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

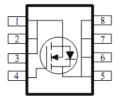
Typical	Applications	
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- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)			
30	5.2 @ V _{GS} = 10V	26			
	$7.5 @ V_{GS} = 4.5V$	21			







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter			Symbol	Limit	Units		
Drain-Source Voltage			V_{DS}	30	V		
Gate-Source Voltage				±20	V		
Continuous Drain Coursetta		T _A =25°C	1	26			
Continuous Drain Current ^a		T _A =70°C	I _D	20	Α		
Pulsed Drain Current ^b				100	'		
Continuous Source Current (Diode Conduction) a	I _S	6.5	Α				
Dawar Dissipation 8		T _A =25°C	P _D	5	W		
Power Dissipation ^a	-	T _A =70°C	' D	3.2	۷V		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

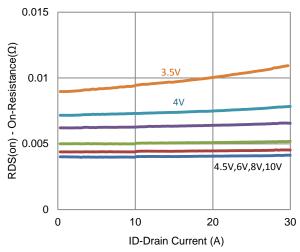
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	2		25] "^	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			5.2	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			7.5	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		21		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.78		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		19			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		5.1		nC	
Gate-Drain Charge	Q_gd	1D = 20 A		8.6			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_1 = 0.75 \Omega,$		4			
Rise Time	t _r	$V_{DS} = 15 \text{ V}, R_L - 0.75 \Omega,$ $I_D = 20 \text{ A},$		11		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		54		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.22		20			
Input Capacitance	C _{iss}			3064			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		288		pF	
Reverse Transfer Capacitance	C_{rss}			264			

Notes

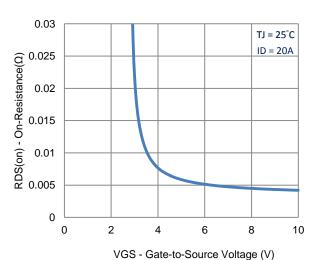
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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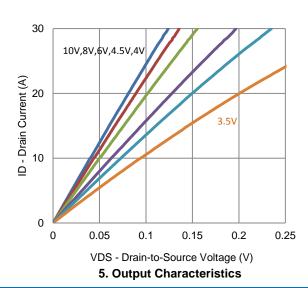
Typical Electrical Characteristics

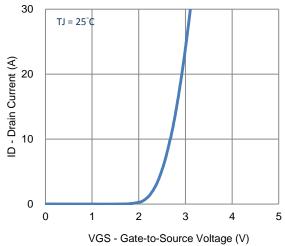


1. On-Resistance vs. Drain Current

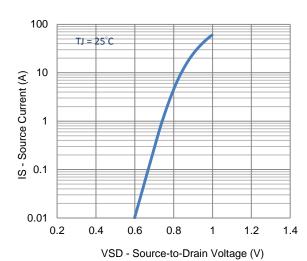


3. On-Resistance vs. Gate-to-Source Voltage

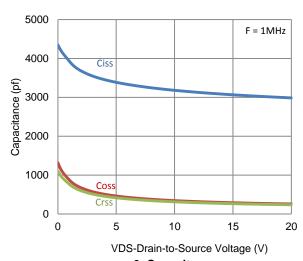




2. Transfer Characteristics

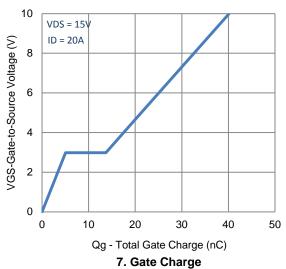


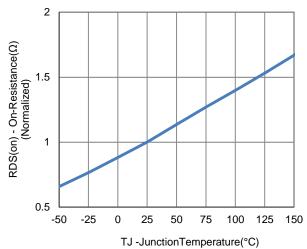
4. Drain-to-Source Forward Voltage

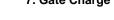


6. Capacitance

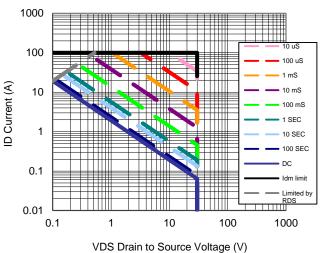
Typical Electrical Characteristics

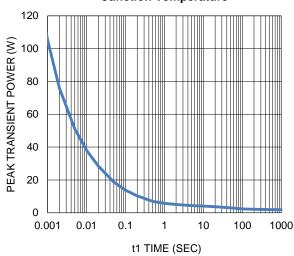






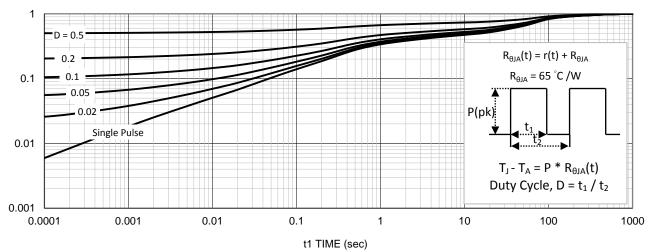






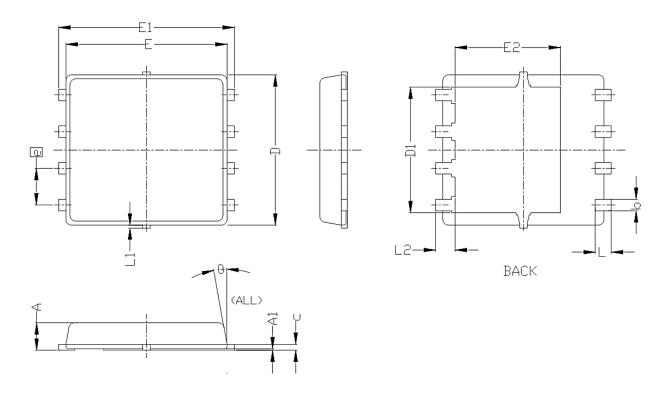
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.020		
С	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0. 55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	